

MP7510DI, MP7511DI, MP7512DI

CMOS QUAD SPST ANALOG SWITCHES (MP7510DI, MP7511DI)

CMOS DUAL SPDT ANALOG SWITCH (MP7512DI)

FEATURES

- Latch-Proof
- Overvoltage Protected
- Low R_{ON} : 75Ω
- Low Dissipation: 3mW
- TTL/CMOS Direct Interface
- Silicon-Nitride Passivated
- Monolithic Dielectrically-Isolated CMOS

GENERAL DESCRIPTION

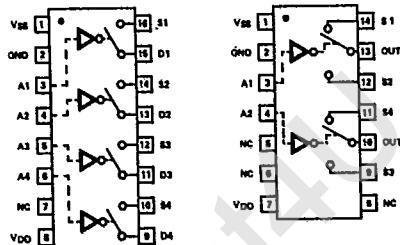
The MP7510DI, MP7511DI and MP7512DI are a family of latch proof dielectrically isolated CMOS switches featuring overvoltage protection up to $\pm 25V$ above the power supplies. These benefits are obtained without sacrificing the low "ON" resistance (75Ω) or low leakage current (400pA), the main features of an analog switch.

The MP7510DI and MP7511DI consist of four independent SPST analog switches packaged in a 16-pin DIP. They differ only in that the digital control logic is inverted. The MP7512DI has two independent SPDT switches packaged in a 14-pin DIP.

Very low power dissipation, overvoltage protection and TTL/CMOS direct interfacing are achieved by combining a unique circuit design and a dielectrically isolated CMOS process. Silicon nitride passivation ensures long term stability while monolithic construction provides reliability.

PIN CONFIGURATIONS

(TOP VIEW)



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CONTROL LOGIC

MP7510DI: Switch "ON" for Address "HIGH"

MP7511DI: Switch "ON" for Address "LOW"

MP7512DI: Address "HIGH" makes S1 to Out-1 and S3 to Out-2

See Section 7 for Ordering Information

MICRO POWER SYSTEMS INC

MP7510DI, MP7511DI, MP7512DI**SPECIFICATIONS (V_{DD} = +15V, V_{SS} = -15V unless otherwise noted)**

COMMERCIAL VERSIONS (J, K)

PARAMETER ⁴	MODEL	VERSION	25°C	0°C to 70°C (N) -25°C to +85°C (D)		UNITS	TEST CONDITIONS
				MIN	MAX		
ANALOG SWITCH							
R _{ON} ¹	All	J, K	100 max		175	Ω	-10V ≤ V _D ≤ +10V I _{DS} = 1.0 mA
R _{ON} vs V _D (V _S)	All	J, K	20 typ			%	
R _{ON} Drift	All	J, K	+0.5 typ			%/°C	
R _{ON} Match	All	J, K	1 typ			%	
R _{ON} Drift Match	All	J, K	0.01 typ			%/°C	V _D = 0, I _{DS} = 1.0 mA
I _D (I _S)OFF ¹	All	J, K	5 max		500	nA	V _D = -10V, V _S = +10V and V _D = +10V, V _S = -10V
I _D (I _S)ON ²	All	J, K	10 max			nA	V _S = V _D = +10V V _S = V _D = -10V
I _{OUT} ¹	MP7512DI	J, K	15 max		1500	nA	V _{S1} = V _{OUT} = ±10V, V _{S2} = ±10V and V _{S2} = V _{OUT} = ±10V, V _{S1} = ±10V
DIGITAL CONTROL							
V _{INL} ¹	All	J, K			0.8	V	
V _{INH} ¹	All	K		2.4		V	
C _{IN}	All	J, K	3 typ			pF	
I _{INH} ¹	All	J, K	10 max			nA	V _{IN} = V _{DD}
I _{INL} ¹	All	J, K	10 max			nA	V _{IN} = 0
DYNAMIC CHARACTERISTICS							
t _{ON}	MP7510DI MP7511DI	J, K J, K	180 typ 350 typ			ns ns	
t _{OFF}	MP7510DI MP7511DI	J, K J, K	350 typ 180 typ			ns ns	V _{IN} = 0 to +3.0V
t _{TRANSITION}	MP7512DI	J, K	300 typ			ns	
C _S (C _D)OFF	All	J, K	8 typ			pF	
C _S (C _D)ON	All	J, K	17 typ			pF	
C _{DS} (C _S -OUT)	All	J, K	1 typ			pF	V _D (V _S) = 0V
C _{DD} (C _S)	All	J, K	0.5 typ			pF	
C _{OUT}	MP7512DI	J, K	17 typ			pF	
Q _{INJ}	All	J, K	30 typ			pC	Measured at S or D terminal. C _L = 1000 pF, V _{IN} = 0 to 3V, V _D (V _S) = +10V to -10V
POWER SUPPLY							
I _{DD} ¹	All	J, K	800 max		800	μA	All digital inputs = V _{INH}
I _{SS} ¹	All	J, K	800 max		800	μA	
I _{DD} ¹	All	J, K	500 max		500	μA	All digital inputs = V _{INL}
I _{SS} ¹	All	J, K	500 max		500	μA	

Notes¹ 100% tested.² Guaranteed, not production tested.³ A pullup resistor, typically 1-2 kΩ is required to make "J" versions TTL compatible.⁴ Specifications subject to change without notice.

CAUTION: The digital control inputs are zener protected; however, permanent damage may occur on unconnected units under high electrostatic fields. Keep unused units in conductive foam at all times. Prior to pulling the devices from the conductive foam, ground the foam to deplete any accumulated charge.

MP7510DI, MP7511DI, MP7512DI**SPECIFICATIONS (V_{DD} = ±15V, V_{SS} = -15V unless otherwise noted)****MILITARY VERSIONS (S, T)**

PARAMETER ⁴	MODEL	VERSION	25°C MAX	-55°C to +125°C		UNITS	TEST CONDITIONS
				MIN	MAX		
ANALOG SWITCH							
R _{ON} ¹	All	S, T	100		175	Ω	-10V ≤ V _D ≤ +10V I _{DS} = 1 mA
I _D (I _S)OFF ¹	All	S, T	3		200	nA	V _D = -10V, V _S = +10V and V _D = +10V, V _S = -10V
I _D (I _S)ON ²	All	S, T	10		600	nA	V _S = V _D = +10V and V _S = V _D = -10V
I _{OUT} ¹	MP7512DI	S, T	9		600	nA	V _{S1} = V _{OUT} = ±10V V _{S2} = ±10V and V _{S2} = V _{OUT} = ±10V V _{S1} = ±10V
DIGITAL CONTROL							
V _{INL} ¹	All	S, T			0.8	V	
MP7510DI	S		2.4			V	
MP7511DI	T		2.4			V	
MP7512DI	S		3.0			V	
I _{INH} ¹	All	S, T	10			nA	V _{IN} = V _{DD}
I _{INL} ¹	All	S, T	10			nA	V _{IN} = 0
DYNAMIC CHARACTERISTICS							
t _{ON} ²	MP7510DI MP7511DI	S, T	1.0			μs	V _{IN} = 0 to +3V
t _{OFF} ²	MP7510DI MP7511DI	S, T	1.0			μs	
t _{TRANSITION} ²	MP7512DI	S, T	1.0			μs	
POWER SUPPLY							
I _{DD} ¹	All	S, T			800	μA	All digital inputs = V _{INH}
I _{SS} ¹	All	S, T			800	μA	
I _{DD} ¹	All	S, T			500	μA	All digital inputs = V _{INL}
I _{SS} ¹	All	S, T			500	μA	

ABSOLUTE MAXIMUM RATINGS

V _{DD} to Gnd	+17V	Digital Input Voltage Range	0V to V _{DD}
V _{SS} to Gnd	-17V	Power Dissipation (Package)	
Oversupply at V _D (V _S) (1 second surge)	V _{DD} +25V or V _{SS} -25V	Up to +75°C	450 mW
(Continuous)	V _{DD} +20V or V _{SS} -20V	Derates above +75°C by	6 mW/°C
Switch Current (I _{DS} , Continuous)	50 mA	Storage Temperature	-65°C to +150°C
Switch Current (I _{DS} , Surge) 1 ms Duration, 10% Duty Cycle	150 mA	Operating Temperature	
		Plastic (J, K Versions)	0°C to +70°C
		Ceramic (J, K Versions)	-25°C to +85°C
		Ceramic (S, T Versions)	-55°C to +125°C

Notes¹ 100% tested.² Guaranteed, not production tested.³ A pullup resistor, typically 1-2 kΩ is required to make the MP7511DISD and MP7512DISD TTL compatible.⁴ Specifications subject to change without notice.